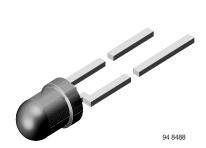




Resistor LED for 12 V Supply Voltage



FEATURES

- With current limiting resistor for 12 V
- Cost effective: save space and resistor cost
- Standard Ø 3 mm (T-1) package
- Very wide viewing angle
- · Luminous intensity categorized
- Luminous intensity and color are measured at 12 V

DESCRIPTION

These devices are developed for the automotive industry and other industries which use 12 V sources.

The TLRD410. series contains an integrated resistor for current limiting in series with the LED chip. This allows the lamp to be driven from a 12 V source without an external current limiter.

The luminous intensity of such an LED is measured at constant voltage of 12 V. These tinted diffused lamps provide a wide off-axis viewing angle.

These LEDs are intended for space critical applications such as automobile instrument panels, switches and others which are driven from a 12 V source.

APPLICATIONS

- Status light in cars and other applications with a 12 V source
- OFF / ON indicator in cars and other applications with a 12 V source
- · Background illumination for switches
- · Off / On indicator in switches

ABSOLUTE MAXIMUM RATINGS ¹⁾								
PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT				
Reverse voltage		V _R	6	V				
Forward voltage	T _{amb} ≤ 65 °C	V _F	16	V				
Power dissipation	T _{amb} ≤ 65 °C	P _V	240	mW				
Junction temperature		T _j	100	°C				
Storage temperature range		T _{stg}	- 55 to + 100	°C				
Soldering temperature	$t \le 5$ s, 2 mm from body	T _{sd}	260	°C				
Thermal resistance junction/ambient		R _{thJA}	150	K/W				

Note:

¹⁾ T_{amb} = 25 °C unless otherwise specified

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OPTICAL AND ELECTRICAL CHARACTERISTICS ¹⁾ , RED										
PARAMETER	TEST CONDITION	PART	SYMBOL	MIN	TYP.	MAX	UNIT			
Luminous intensity	V _F = 12 V	TLRD4100	I _V	25	40		mcd			
		TLRD4106	I _V	25		80	mcd			
Dominant wavelength	V _F = 12 V		λ_{d}		648		nm			
Peak wavelength	V _F = 12 V		λ_{p}		650		nm			
Angle of half intensity	V _F = 12 V		φ		± 22		deg			
Forward current	V _S = 12 V		I _F		10	13	mA			
Breakdown voltage	I _R = 10 μA		V_{BR}	6	20		V			
Junction capacitance	V _R = 0, f = 1 MHz		C _j		50		pF			

Note:

TYPICAL CHARACTERISTICS

 T_{amb} = 25 °C unless otherwise specified

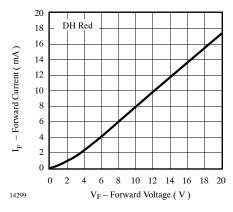


Figure 1. Forward Current vs. Forward Voltage

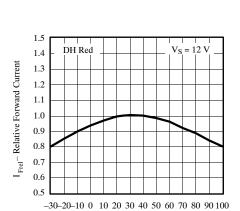


Figure 2. Relative Forward Current vs. Ambient Temperature

Tamb - Ambient Temperature (°C)

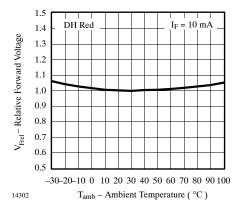


Figure 3. Relative Forward Voltage vs. Ambient Temperature

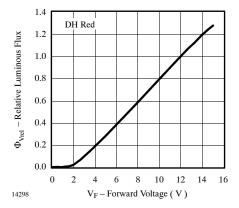


Figure 4. Relative Luminous Flux vs. Forward Voltage

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 $^{^{1)}}$ T_{amb} = 25 °C unless otherwise specified





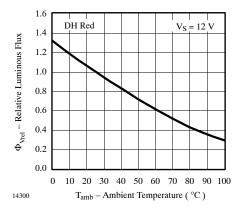


Figure 5. Rel. Luminous Flux vs. Ambient Temperature

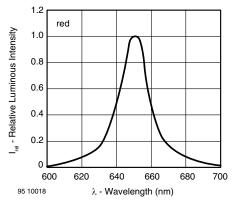


Figure 6. Relative Intensity vs. Wavelength

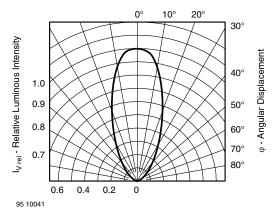
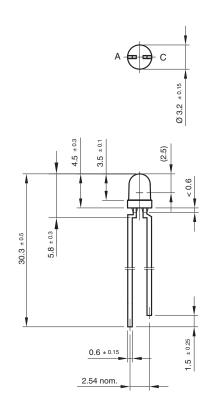


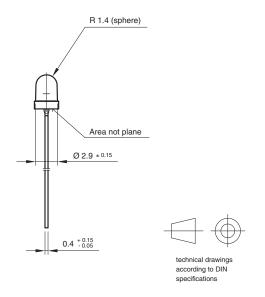
Figure 7. Rel. Luminous Intensity vs. Angular Displacement

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PACKAGE DIMENSIONS IN MM





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Ozone Depleting Substances Policy Statement

It is the policy of Vishay Semiconductor GmbH to

- 1. Meet all present and future national and international statutory requirements.
- 2. Regularly and continuously improve the performance of our products, processes, distribution and operating systems with respect to their impact on the health and safety of our employees and the public, as well as their impact on the environment.

It is particular concern to control or eliminate releases of those substances into the atmosphere which are known as ozone depleting substances (ODSs).

The Montreal Protocol (1987) and its London Amendments (1990) intend to severely restrict the use of ODSs and forbid their use within the next ten years. Various national and international initiatives are pressing for an earlier ban on these substances.

Vishay Semiconductor GmbH has been able to use its policy of continuous improvements to eliminate the use of ODSs listed in the following documents.

- 1. Annex A, B and list of transitional substances of the Montreal Protocol and the London Amendments respectively
- 2. Class I and II ozone depleting substances in the Clean Air Act Amendments of 1990 by the Environmental Protection Agency (EPA) in the USA
- 3. Council Decision 88/540/EEC and 91/690/EEC Annex A, B and C (transitional substances) respectively.

Vishay Semiconductor GmbH can certify that our semiconductors are not manufactured with ozone depleting substances and do not contain such substances.

> We reserve the right to make changes to improve technical design and may do so without further notice.

Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer. Should the buyer use Vishay Semiconductors products for any unintended or unauthorized application, the buyer shall indemnify Vishay Semiconductors against all claims, costs, damages, and expenses, arising out of, directly or indirectly, any claim of personal damage, injury or death associated with such unintended or unauthorized use.

Vishay Semiconductor GmbH, P.O.B. 3535, D-74025 Heilbronn, Germany

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